

UTC2SA1507 PNP EPITAXIAL SILICON TRANSISTORS

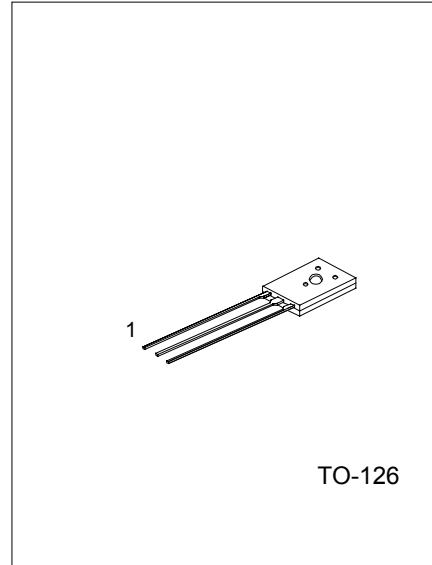
SWITCHING TRANSISTOR

APPLICAITONS

*Color TV audio output, converters, inverters.

FEATURES

- *High breakdown voltage
- *Large current capacitance.
- *High-speed switching



1:EMITTER 2:COLLECTOR 3:BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CB0}	-180	V
Collector-Emitter Voltage	V _{CEO}	-160	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current	I _c	-1.5	A
Collector Current (Peak)	I _{cp}	-2.5	A
Collector Dissipation	P _c	1.5	W
Collector Dissipation(T _c =25°C)	P _c	10	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	I _c =-10μA, I _E =0	-180			V
Collector-to-Base Breakdown Voltage	V _{(BR)CEO}	I _c = -1mA, R _{BE} =∞	-160			V
Emitter-to-Base Breakdown Voltage	V _{(BR) EBO}	I _c =0, I _E = -10μA	-6			V
Collector Cut-Off Current	I _{CBO}	V _{CB} = -120V, I _E =0			-0.1	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} = -4V, I _c =0			-0.1	μA
DC Current Gain	h _{FE1}	V _{CE} = -5V, I _c = -100mA	100		400	
	h _{FE2}	V _{CE} = -5V, I _c = -10mA	90			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = -500mA, I _B = -50mA		-0.2	-0.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _c = -500mA, I _B = -50mA		-0.83	-1.2	V
Gain Bandwidth Product	f _T	V _{CE} = -10V, I _c = -50mA		120		MHz
Output Capacitance	C _{ob}	V _{CB} = -10V, f=1MHz		22		pF
Turn-On Time	t _{on}	See specified Test Circuit		0.04		μs

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1

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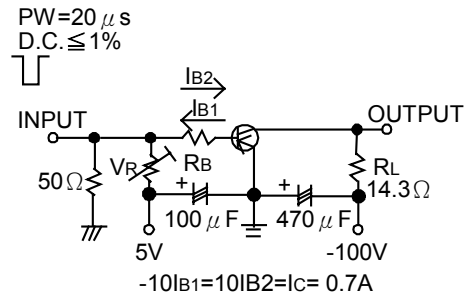
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PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Storage Time	tstg	See specified Test Circuit		0.7		μs
Fall Time	tf	See specified Test Circuit		0.04		μs

CLASSIFICATION OF hFE1

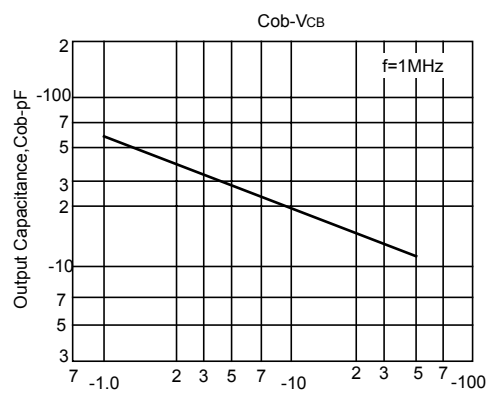
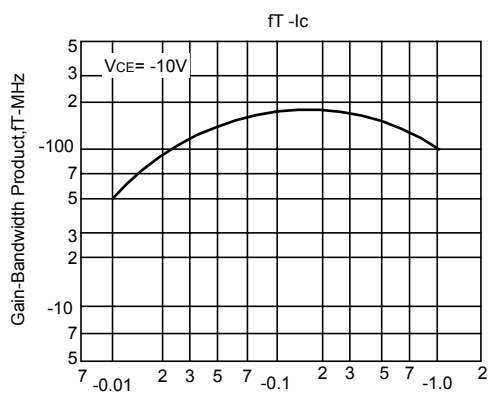
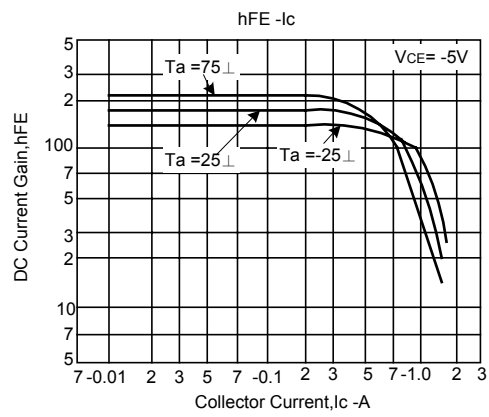
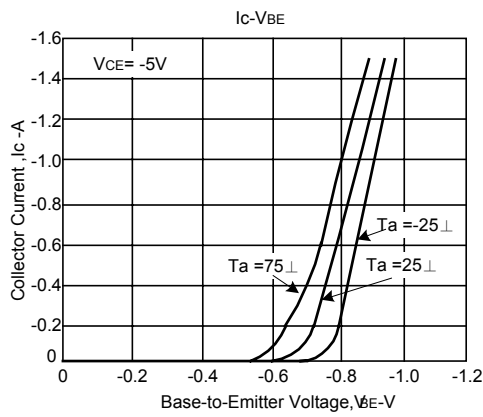
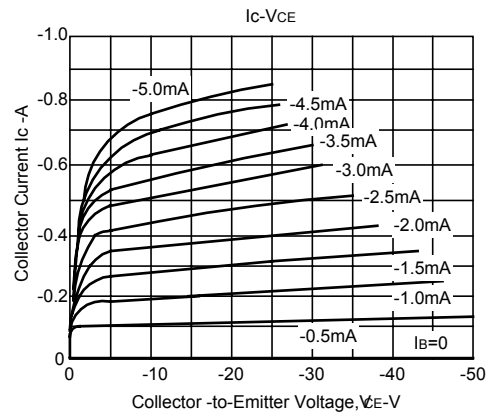
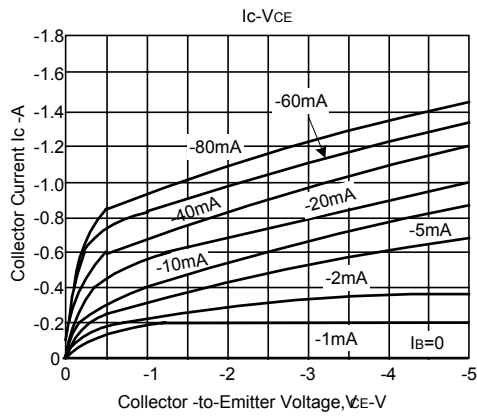
RANK	R	S	T
RANGE	100-200	140-280	200-400

SWITCHING TIME TEST CIRCUIT

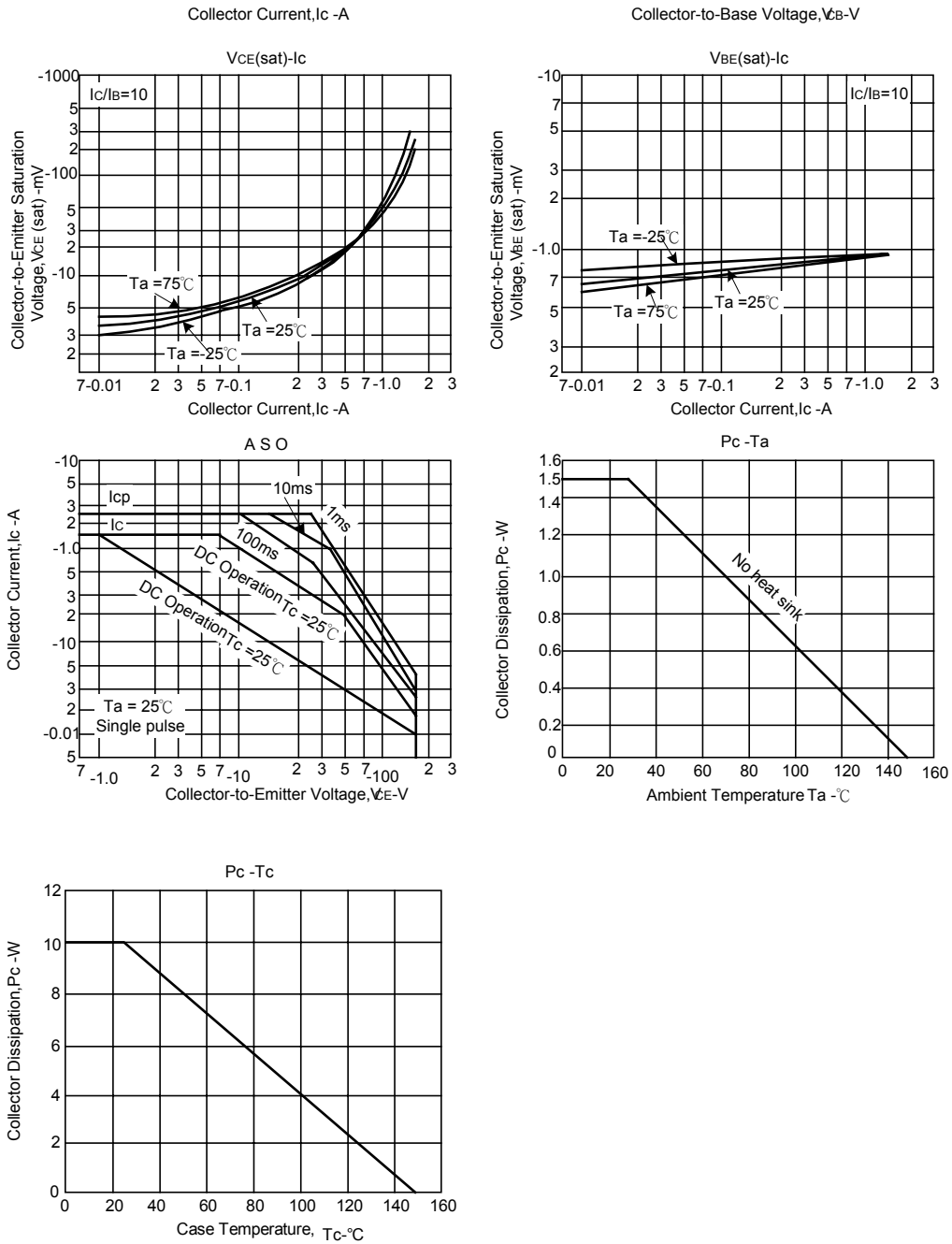


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TYPICAL CHARACTERISTICS



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